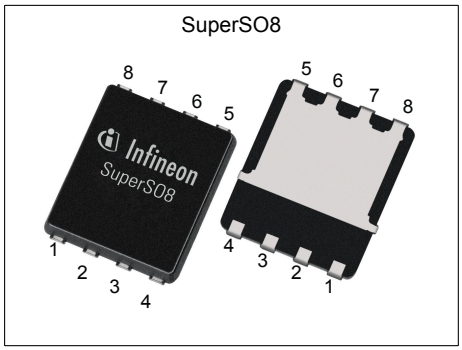
MOSFET

OptiMOS™ Power-MOSFET, 34 V



Features

Features

- Optimized for 5V driver application (Wireless Charging)
- Low FOM_{SW} for High Frequency SMPS
- 100% Avalanche tested
- Improved switching behaviour
- N-channel
- Very low on-resistance $R_{DS(on)}$ @ V_{GS}=4.5 V
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Qualified according to JEDEC[1] for target applications
- Superior thermal resistance
- Pb-free plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

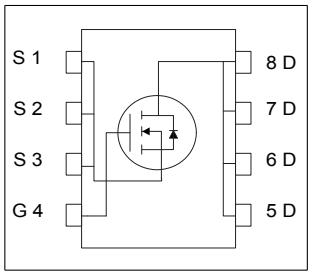


Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	34	V
$R_{DS(on),max}$	9	mΩ
I_D	13	A
Q_{OSS}	10	nC
Q_G(0V..4.5V)	7.2	nC

Type / Ordering Code	Package	Marking	Related Links
BSC0996NS	PG-TDSON-8	0996NS	-

[1] J-STD20 and JESD22

Table of Contents

1 Maximum ratings

at T_A=25 °C, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	I_D	- -	- -	13 8.5	A	V_{GS}=10 V, T_A=100 °C V_{GS}=10 V, T_A=100 °C
Pulsed drain current[1]	$I_{D,pulse}$	-	-	52	A	T_A=25 °C
Avalanche current, single pulse[2]	I_{AS}	-	-	35	A	T_C=25 °C
Avalanche energy, single pulse	E_{AS}	-	-	10	mJ	I_D=25 A, R_{GS}=25 Ω
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	2.5	W	T_A=25 °C, R_{thJA}=50 K/W[3]
Operating and storage temperature	T_j, T_{stg}	-55	-	150	°C	IEC climatic category; DIN IEC 68-1: 55/150/56

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case, bottom	R_{thJC}	-	-	4.6	K/W	-
Thermal resistance, junction - case, top	R_{thJC}	-	-	20	K/W	-
Device on PCB, 6 cm^2 cooling area[3]	R_{thJA}	-	-	50	K/W	-

[1] See Diagram 3 for more detailed information
[2] See Diagram 13 for more detailed information
[3] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

3 Electrical characteristics

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	34	-	-	V	V_{GS}=0 V, I_D=1 mA
Gate threshold voltage	$V_{GS(th)}$	1.2	-	2	V	V_{DS}=V_{GS}, I_D=250 µA
Zero gate voltage drain current	I_{DSS}	- -	0.1 10	1 100	µA	V_{DS}=34 V, V_{GS}=0 V, T_j=25 °C V_{DS}=34 V, V_{GS}=0 V, T_j=125 °C
Gate-source leakage current	I_{GSS}	-	10	100	nA	V_{GS}=16 V, V_{DS}=0 V
Drain-source on-state resistance	$R_{DS(on)}$	- -	10 8	12 9	mΩ	V_{GS}=4.5 V, I_D=8 A V_{GS}=10 V, I_D=8 A
Gate resistance[1)]	R_G	1.5	3	6.0	Ω	-
Transconductance	g_{fs}	13	26	-	S	|V_{DS}|>2|I_D|$R_{DS(on)max}$, I_D=8 A

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance[1)]	C_{iss}	-	1100	1500	pF	V_{GS}=0 V, V_{DS}=15 V, f=1 MHz
Output capacitance[1)]	C_{oss}	-	390	520	pF	V_{GS}=0 V, V_{DS}=15 V, f=1 MHz
Reverse transfer capacitance	C_{rss}	-	25	-	pF	V_{GS}=0 V, V_{DS}=15 V, f=1 MHz
Turn-on delay time	$t_{d(on)}$	-	9.7	-	ns	V_{DD}=15 V, V_{GS}=4.5 V, I_D=8 A, $R_{G,ext}$=1.6 Ω
Rise time	t_r	-	4.4	-	ns	V_{DD}=15 V, V_{GS}=4.5 V, I_D=8 A, $R_{G,ext}$=1.6 Ω
Turn-off delay time	$t_{d(off)}$	-	8.9	-	ns	V_{DD}=15 V, V_{GS}=4.5 V, I_D=8 A, $R_{G,ext}$=1.6 Ω
Fall time	t_f	-	5.4	-	ns	V_{DD}=15 V, V_{GS}=4.5 V, I_D=8 A, $R_{G,ext}$=1.6 Ω

Table 6 Gate charge characteristics[2)]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	3.2	-	nC	V_{DD}=15 V, I_D=8 A, V_{GS}=0 to 4.5 V
Gate charge at threshold	$Q_{g(th)}$	-	1.7	-	nC	V_{DD}=15 V, I_D=8 A, V_{GS}=0 to 4.5 V
Gate to drain charge	Q_{gd}	-	1.6	-	nC	V_{DD}=15 V, I_D=8 A, V_{GS}=0 to 4.5 V
Switching charge	Q_{sw}	-	3.0	-	nC	V_{DD}=15 V, I_D=8 A, V_{GS}=0 to 4.5 V
Gate charge total	Q_g	-	7.2	-	nC	V_{DD}=15 V, I_D=8 A, V_{GS}=0 to 4.5 V
Gate plateau voltage	$V_{plateau}$	-	2.8	-	V	V_{DD}=15 V, I_D=8 A, V_{GS}=0 to 4.5 V
Gate charge total[1)]	Q_g	-	15	20	nC	V_{DD}=15 V, I_D=8 A, V_{GS}=0 to 10 V
Gate charge total, sync. FET	$Q_{g(sync)}$	-	6.2	-	nC	V_{DS}=0.1 V, V_{GS}=0 to 4.5 V
Output charge[1)]	Q_{oss}	-	10	13	nC	V_{DD}=15 V, V_{GS}=0 V

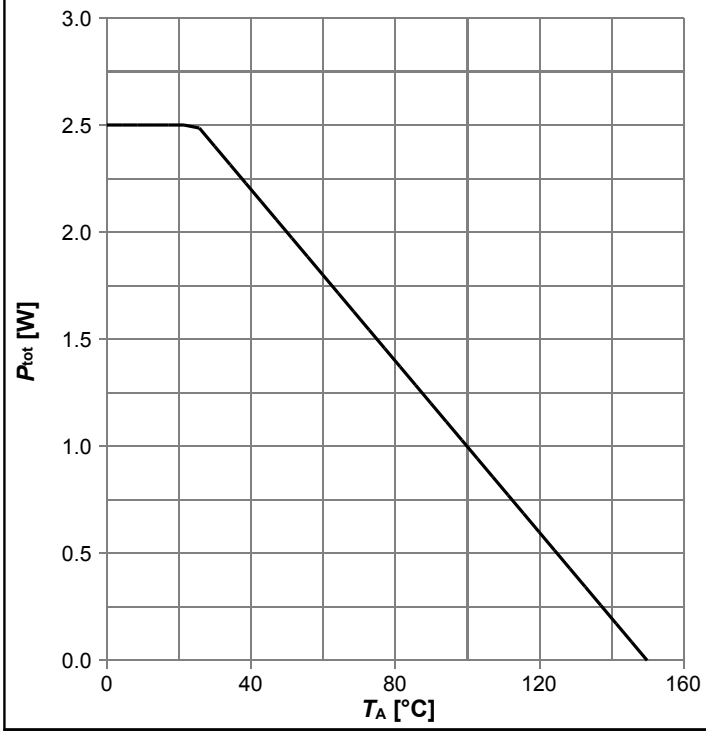
[1)] Defined by design. Not subject to production test.
[2)] See ″Gate charge waveforms″ for parameter definition

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	2	A	T_A=25 °C
Diode pulse current	$I_{S,pulse}$	-	-	52	A	T_A=25 °C
Diode forward voltage	V_{SD}	-	0.77	1.1	V	V_{GS}=0 V, I_F=2.3 A, T_j=25 °C
Reverse recovery charge	Q_{rr}	-	10	-	nC	V_R=15 V, I_F=I_S, di_F/dt=400 A/µs

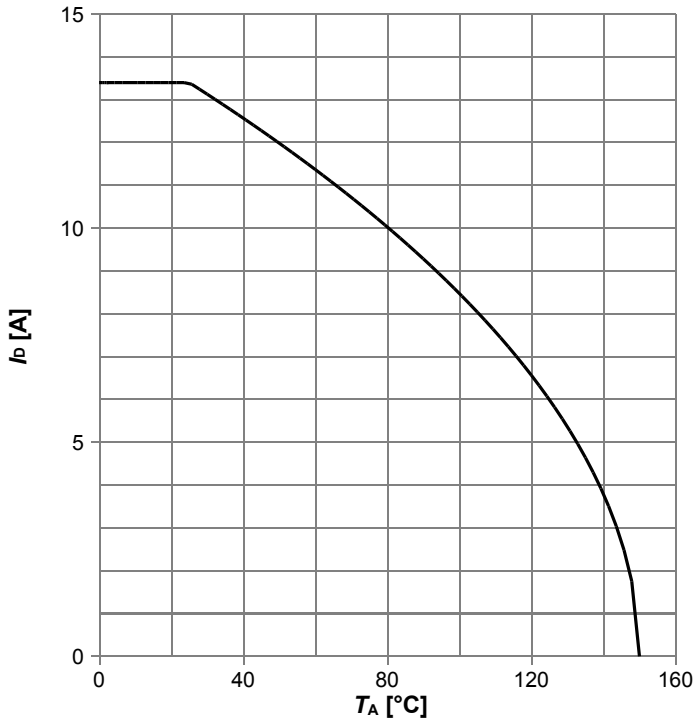
4 Electrical characteristics diagrams

Diagram 1: Power dissipation



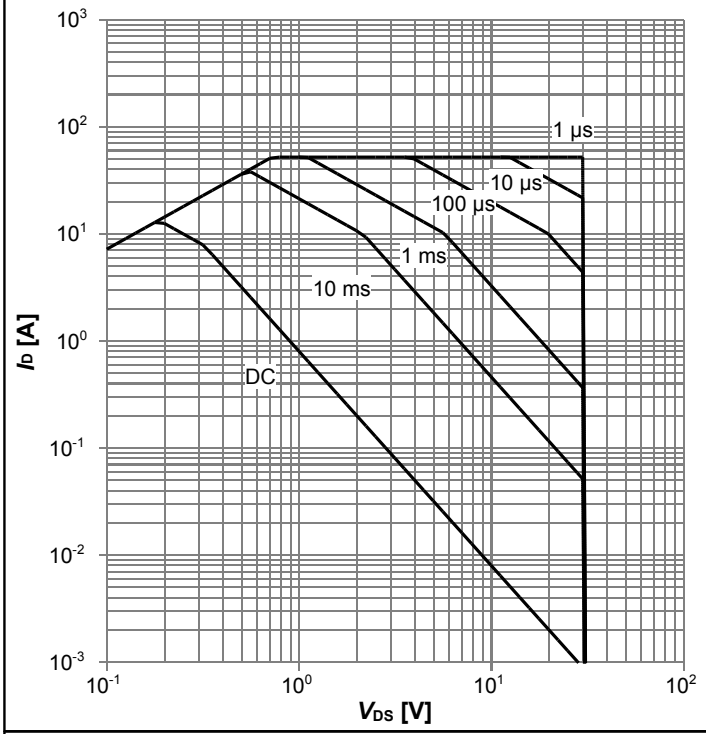
$P_{tot}=f(T_A)$

Diagram 2: Drain current



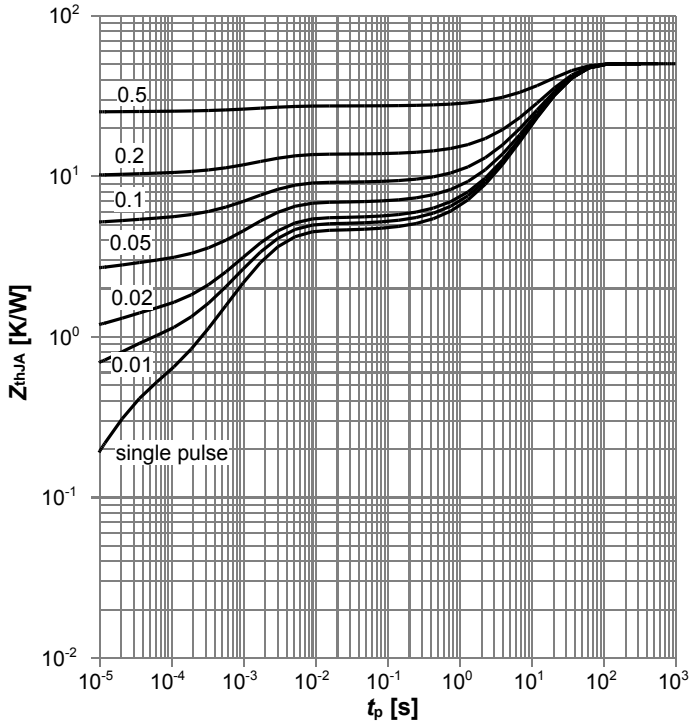
$I_D=f(T_A)$; parameter: V_{GS}

Diagram 3: Safe operating area



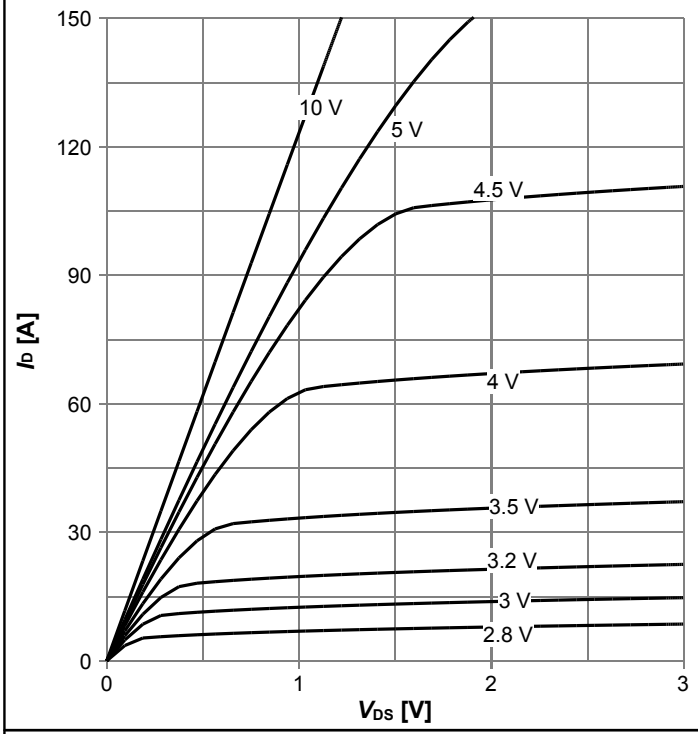
$I_D=f(V_{DS})$; T_A=25 °C; D=0; parameter: t_p

Diagram 4: Max. transient thermal impedance



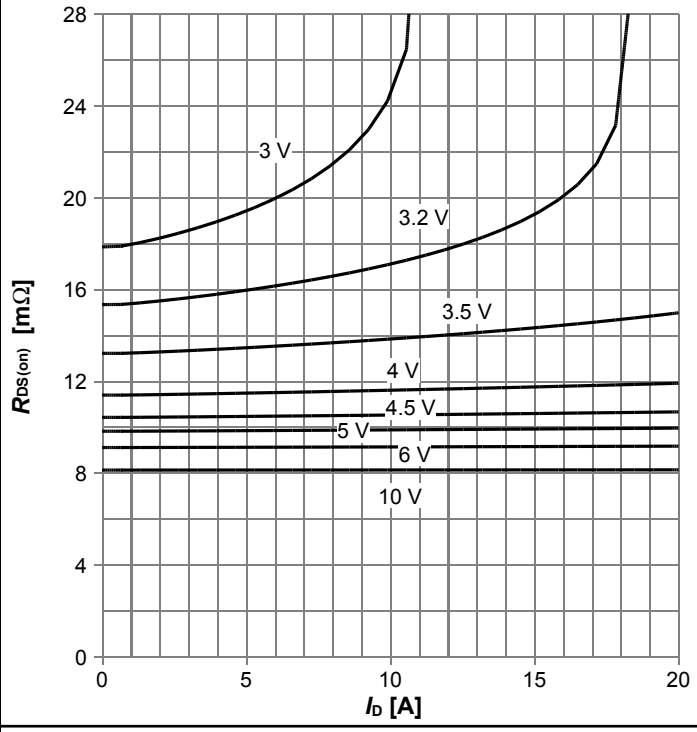
$Z_{thJA}=f(t_p)$; parameter: $D=t_p/T$

Diagram 5: Typ. output characteristics



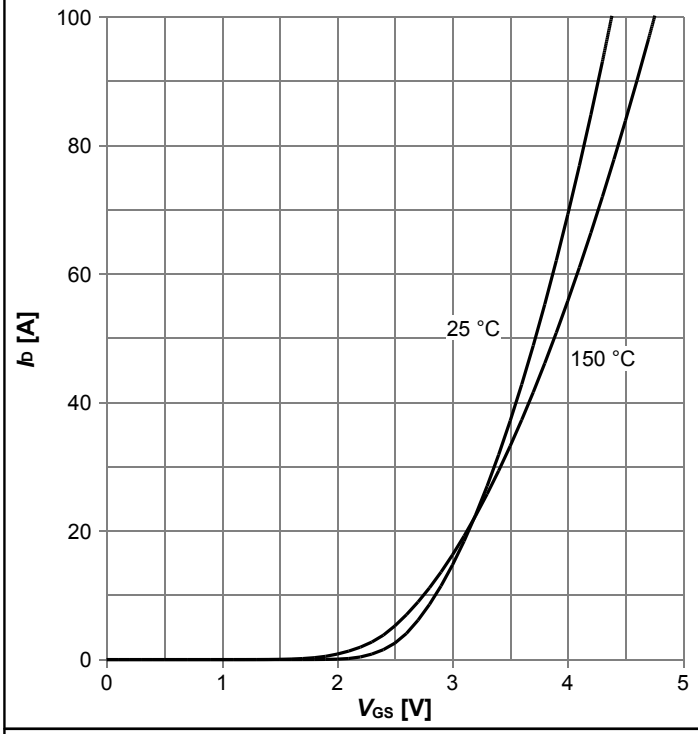
$I_D=f(V_{DS})$; $T_j=25$ °C; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



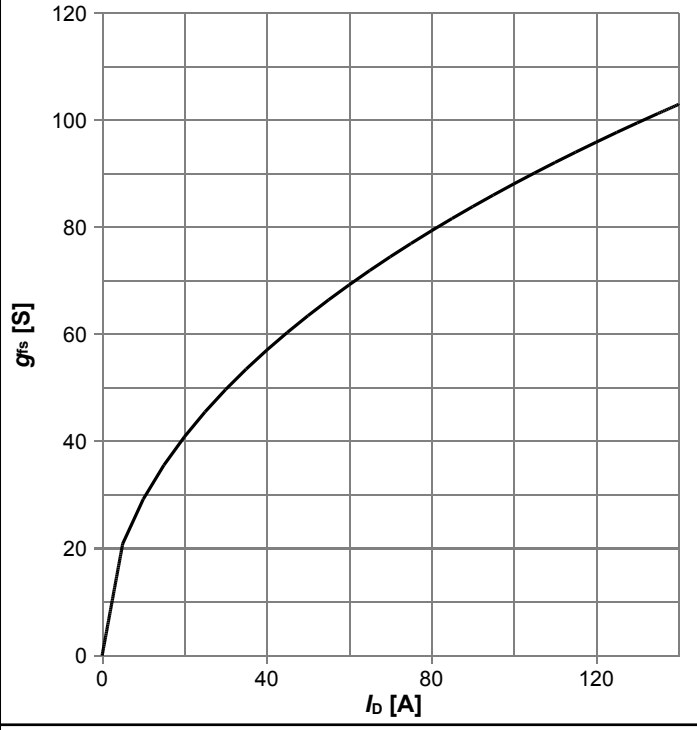
$R_{DS(on)}=f(I_D)$; $T_j=25$ °C; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



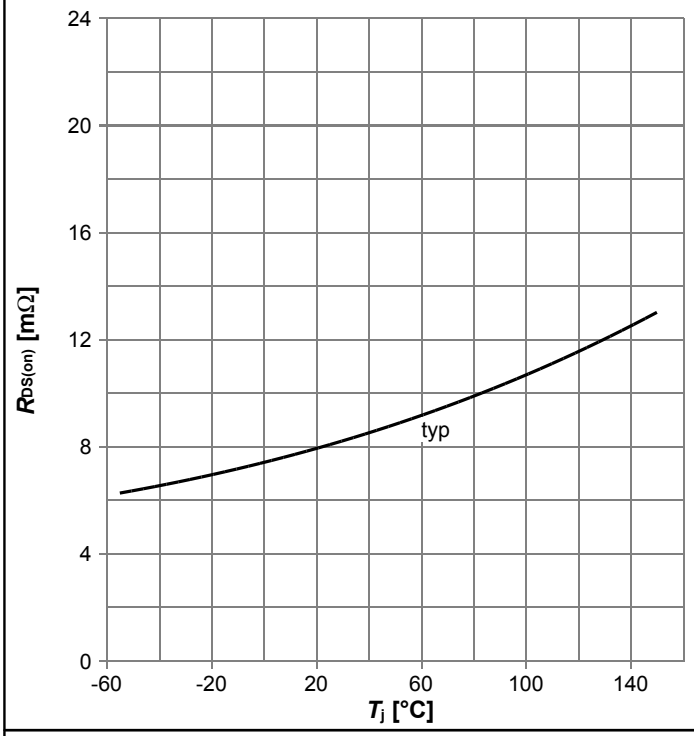
$I_D=f(V_{GS})$; $|V_{DS}|>2|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. forward transconductance



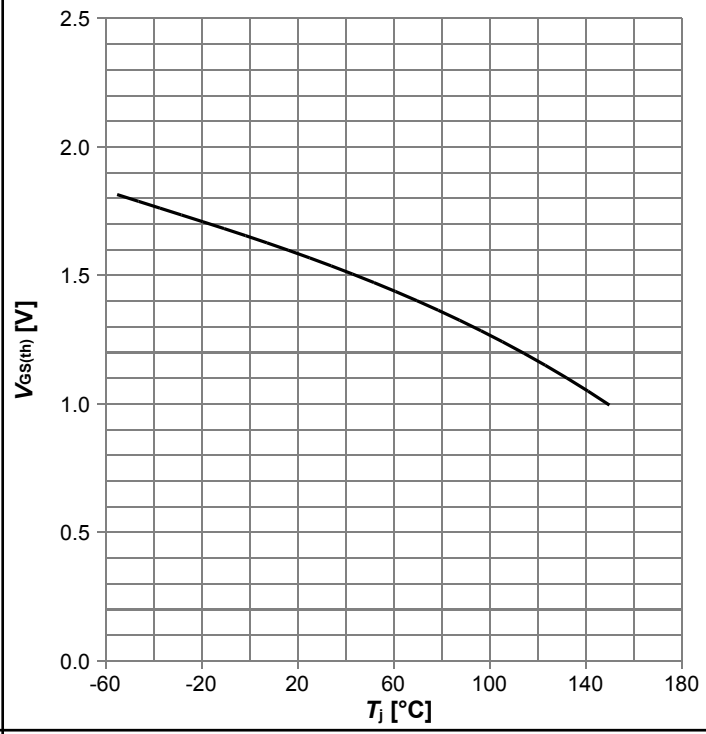
$g_{fs}=f(I_D)$; $T_j=25$ °C

Diagram 9: Drain-source on-state resistance



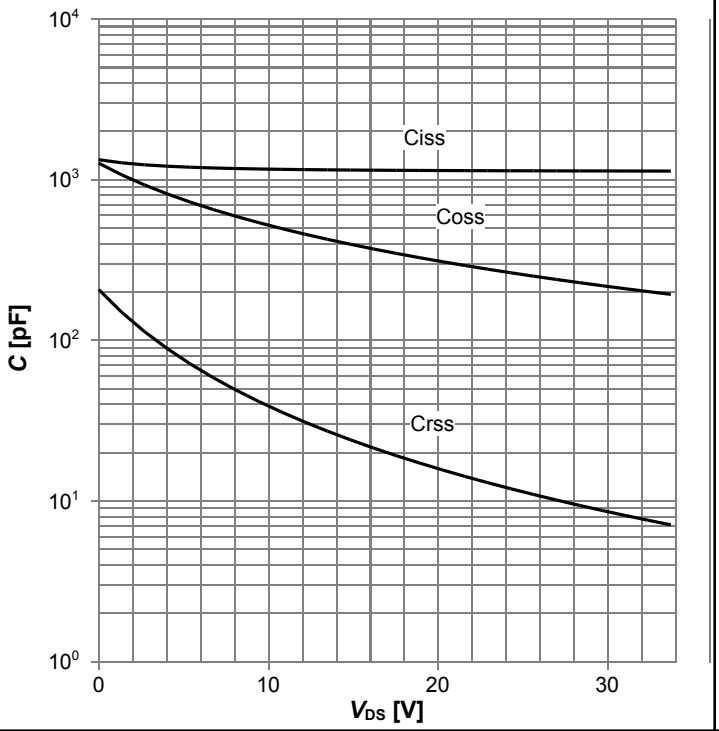
$R_{DS(on)}$=f(T_j); I_D=8 A; V_{GS}=10 V

Diagram 10: Typ. gate threshold voltage



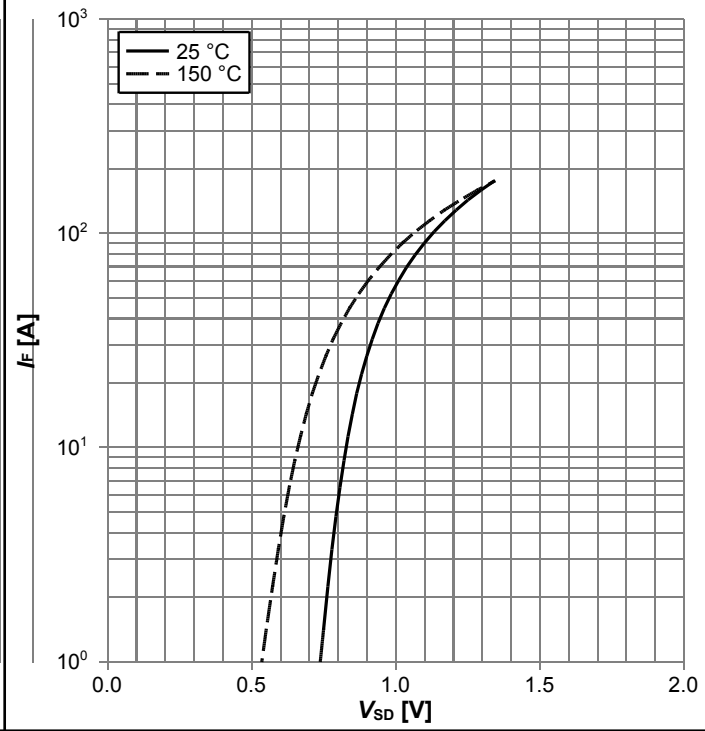
$V_{GS(th)}$=f(T_j); V_{GS}=V_{DS}; I_D=250 µA

Diagram 11: Typ. capacitances



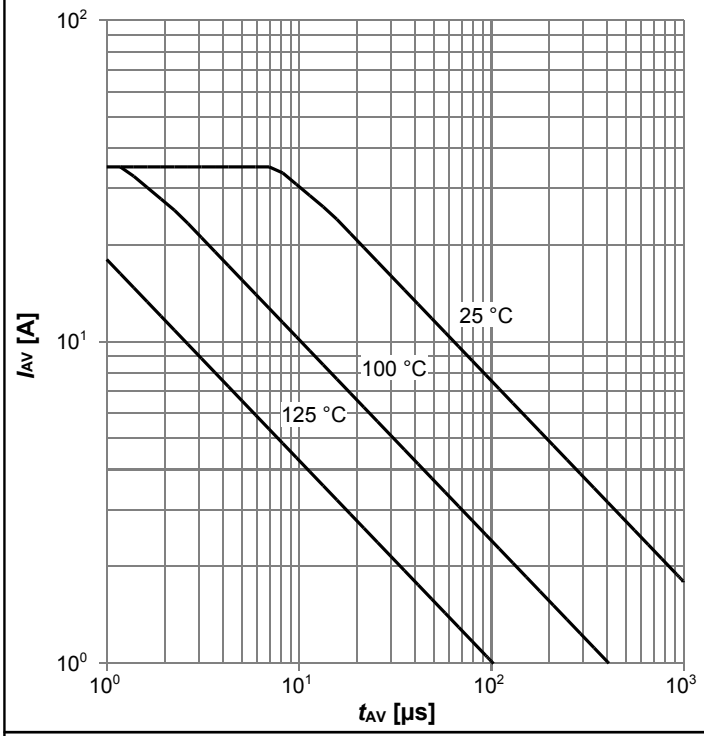
C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

Diagram 12: Forward characteristics of reverse diode



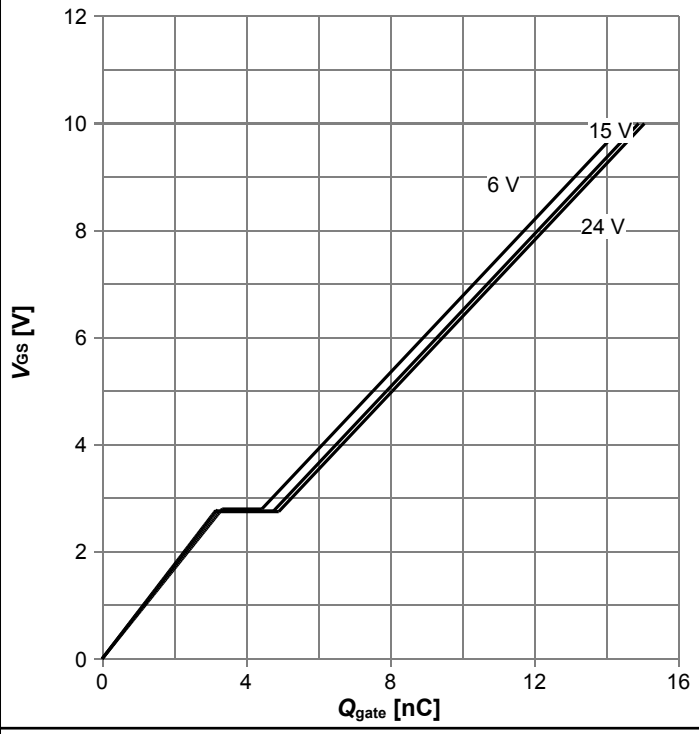
I_F=f(V_{SD}); parameter: T_j

Diagram 13: Avalanche characteristics



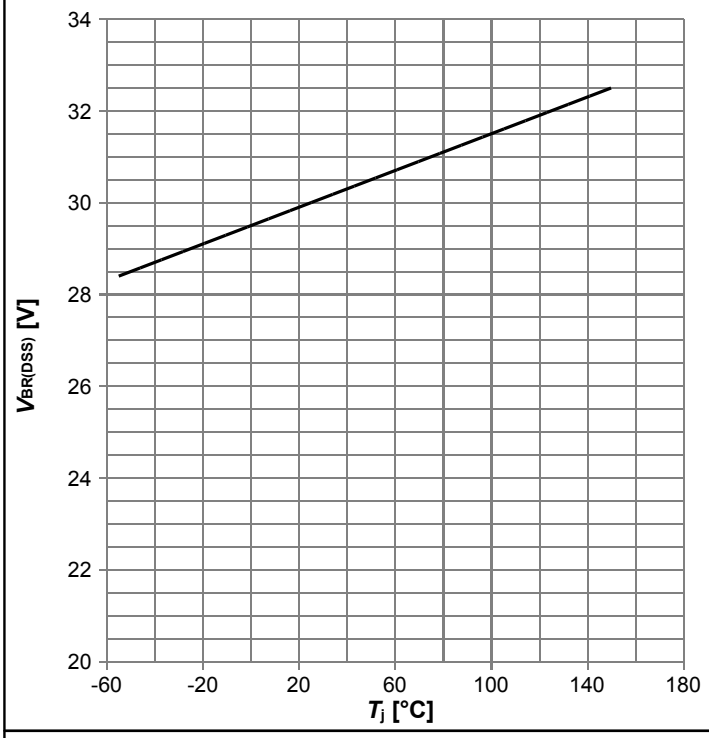
I_{AS}=f(t_{AV}); R_{GS}=25 Ω; parameter: $T_{j(start)}$

Diagram 14: Typ. gate charge



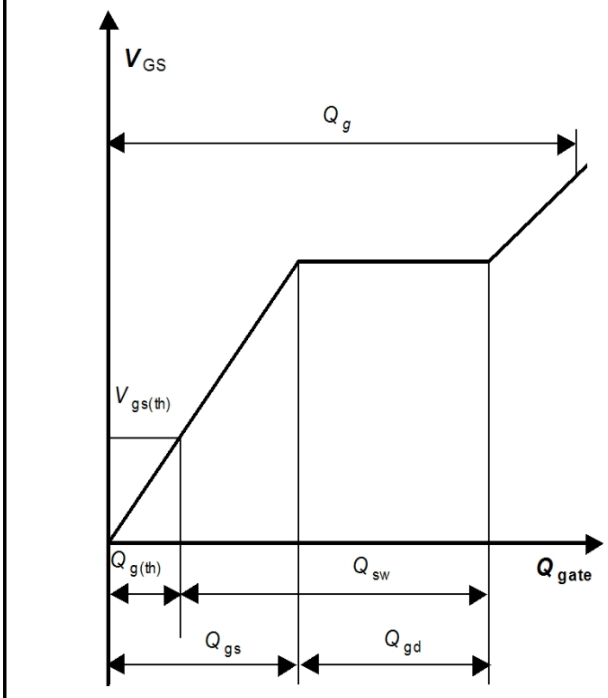
V_{GS}=f(Q_{gate}); I_D=8 A pulsed; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage

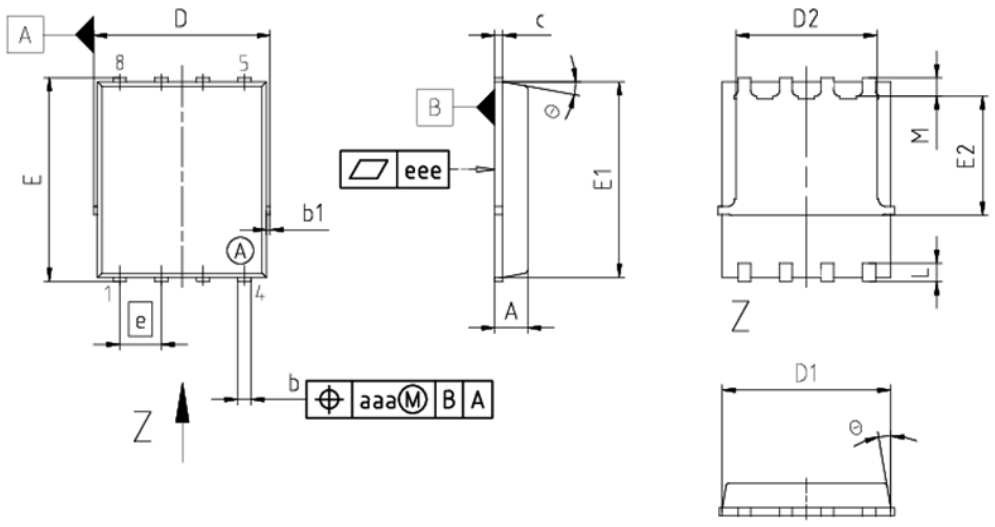


$V_{BR(DSS)}$=f(T_j); I_D=1 mA

Gate charge waveforms



5 Package Outlines



DIM	MILLIMETERS	
	MIN	MAX
A	0.90	1.10
b	0.31	0.54
b1	0.02	0.22
c	0.15	0.35
D	5.15	5.49
D1	4.95	5.35
D2	3.70	4.40
E	5.95	6.35
E1	5.70	6.10
E2	3.40	3.80
e	1.27	
N	8	
L	0.45	0.71
M	0.45	0.75
Θ	8.5°	12°
aaa	0.25	
eee	0.08	

DOCUMENT NO.
Z8B00003332

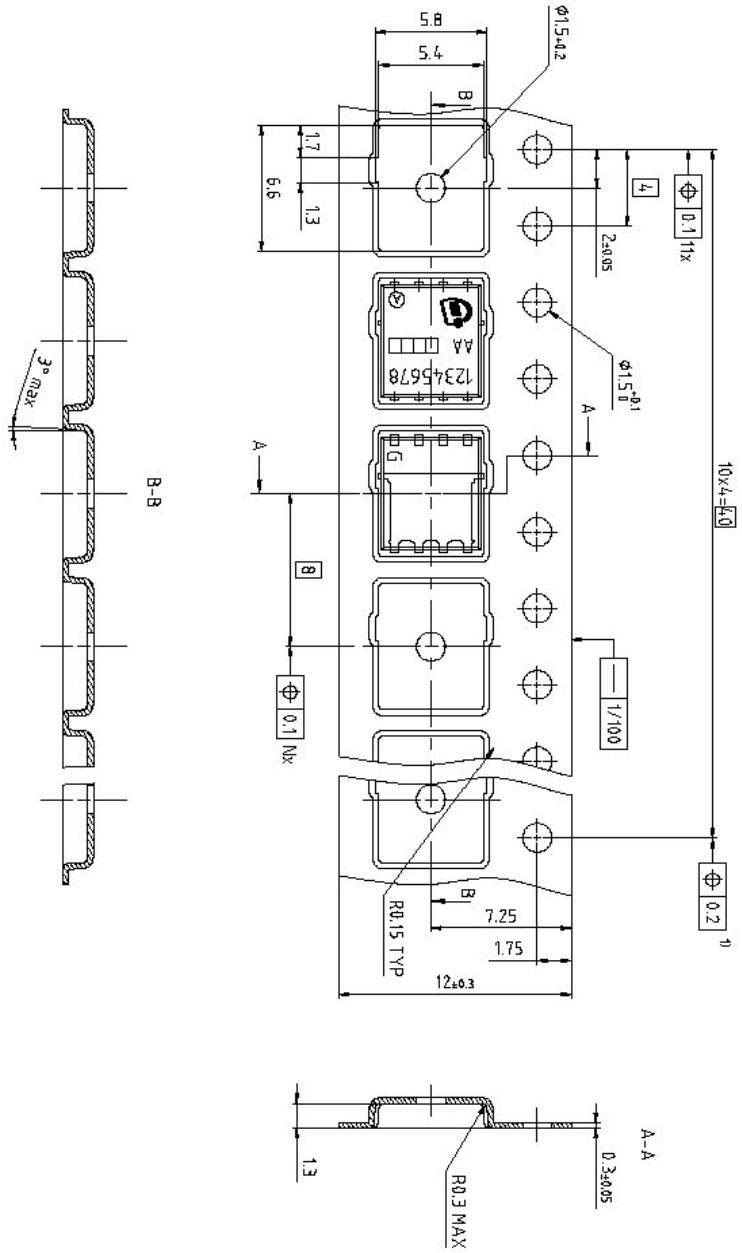
SCALE
0 2 0 2 4mm

EUROPEAN PROJECTION

ISSUE DATE
10-04-2013

REVISION
04

Figure 1 Outline PG-TDSON-8, dimensions in mm



Dimension in mm

Figure 2 Outline Tape (TDSON-8)

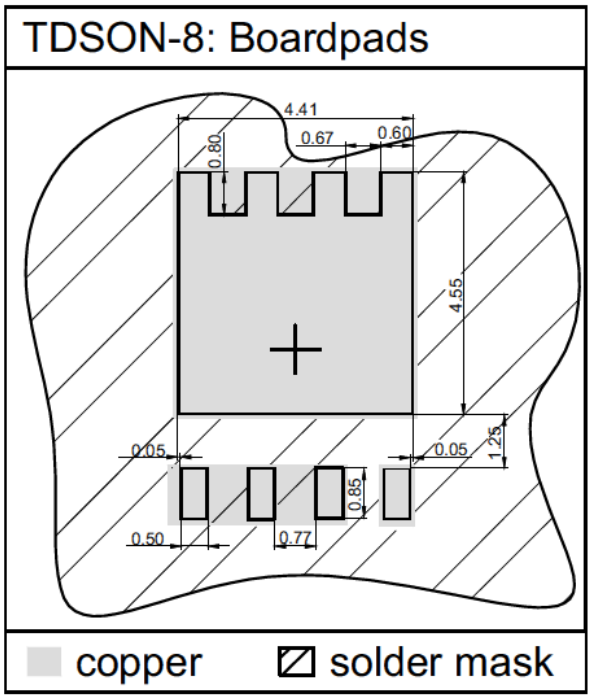


Figure 3 Outline Footprint (TDSON-8)

Revision History

BSC0996NS

Revision: 2016-07-13, Rev. 2.0

Previous Revision		
Revision	Date	Subjects (major changes since last revision)
2.0	2016-07-13	Release of final version

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